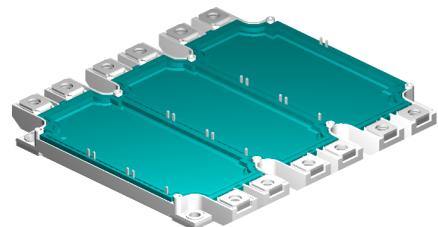
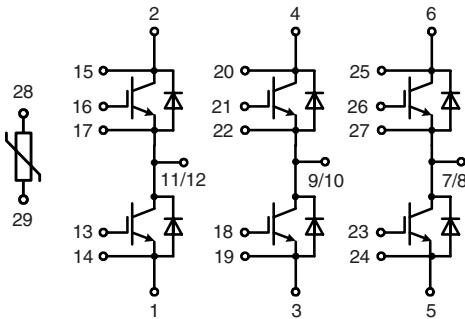


IGBT Modules

Sixpack

I_{C80} = 440 A
V_{CES} = 1200 V
V_{CE(sat)} typ. = 2.2 V



IGBTs

Symbol	Conditions	Maximum Ratings		
V _{CES}	T _{VJ} = 25°C to 125°C	1200	V	
V _{GES}		± 20	V	
I _{C25}	T _C = 25°C	640	A	
I _{C80}	T _C = 80°C	440	A	
RBSOA	R _G = 2.7 Ω; T _{VJ} = 125°C Clamped inductive load; L = 100 μH	I _{OM} = 900 V _{CEK} ≤ V _{CES}	A	
t _{sc} (SCSOA)	V _{CE} = 900 V; V _{GE} = ±15 V; R _G = 2.7 Ω; T _{VJ} = 125°C; non-repetitive; V _{CEmax} ≤ V _{CES}	10	μs	
P _{tot}	T _C = 25°C	2.2	kW	

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)	min.	typ.
V _{CE(sat)}	I _C = 450 A; V _{GE} = 15 V; T _{VJ} = 25°C T _{VJ} = 125°C		2.2 2.5	2.4 V V
V _{GE(th)}	I _C = 18 mA; V _{GE} = V _{CE}	4.5		6.5 V
I _{CES}	V _{CE} = V _{CES} ; V _{GE} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C		6	1 mA 21 mA
I _{GES}	V _{CE} = 0 V; V _{GE} = ± 20 V			600 nA
t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off}	Inductive load, T _{VJ} = 125°C V _{CE} = 600 V; I _C = 450 A V _{GE} = ±15 V; R _G = 2.7 Ω		200	ns
			90	ns
			510	ns
			60	ns
			63	mJ
			45	mJ
C _{ies}	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz	33	nF	
Q _{Gon}	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 450 A	3.3	μC	
R _{thJC}		0.057	K/W	

IXYS reserves the right to change limits, test conditions and dimensions.

Diodes

Symbol	Conditions	Maximum Ratings		
I_{F80}	$T_c = 80^\circ\text{C}$	450	A	
I_{FRM}	$t_p = 1 \text{ ms}$	900	A	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 450 \text{ A}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^\circ\text{C}$		2.1	V
I_{RM}	$I_F = 450 \text{ A}; dI_F/dt = 3500 \text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}; V_R = 800 \text{ V}$	200		A
R_{thJC}		0.075		K/W

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^\circ\text{C}$	4.75	5.0	5.25 kΩ
$B_{25/50}$			3375	K

Module

Symbol	Conditions	Maximum Ratings		
T_{VJ}	operating	-40...+125		°C
T_{JM}		+150		°C
T_{stg}		-40...+125		°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500		V~
M_d	Mounting torque (M5) Terminal connection torque (M6)	3 - 6		Nm
		3 - 6		Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{term-chip}^{*)}$	Resistance terminal to chip	0.55		mΩ
d_s	Creepage distance on surface	12.7		mm
d_A	Strike distance in air	10		mm
R_{thCH}	with heatsink compound	0.01		K/W
Weight		900		g

^{*)} $V = V_{CE(sat)} + 2x R_{term-chip} \cdot I_C$ resp. $V = V_F + 2x R_{term-chip} \cdot I_F$

Dimensions in mm (1 mm = 0.0394")

